



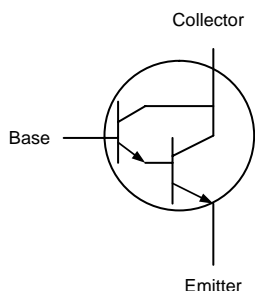
# FUKUCOM COMPANY LTD.

## 福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.  
TEL: 852-2790 0314 FAX: 852-2790 0206

### BC517

#### NPN Silicon Darlington Transistor



1. Collector 2. Base 3. Emitter

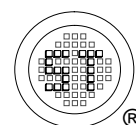
TO-92 Plastic Package  
Weight approx. 0.19g

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	40	V
Collector Emitter Voltage	V <sub>CES</sub>	30	V
Emitter Base Voltage	V <sub>EBO</sub>	10	V
Collector Current	I <sub>C</sub>	500	mA
Total Power Dissipation	P <sub>tot</sub>	625	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>S</sub>	- 55 to + 150	°C

#### Characteristics (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 20 mA	h <sub>FE</sub>	30,000	-	-	-
Collector Saturation Voltage at I <sub>C</sub> = 100 mA, I <sub>B</sub> = 0.1 mA	V <sub>CEsat</sub>	-	-	1	V
Base Emitter On Voltage at V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA	V <sub>BE(on)</sub>	-	-	1.4	V
Collector Base Breakdown Voltage at I <sub>C</sub> = 100 μA	V <sub>(BR)CBO</sub>	40	-	-	V
Collector Emitter Breakdown Voltage at I <sub>C</sub> = 2 mA	V <sub>(BR)CES</sub>	30	-	-	V
Emitter Base Breakdown Voltage at I <sub>E</sub> = 100 μA	V <sub>(BR)EBO</sub>	10	-	-	V
Collector Cutoff Current at V <sub>CE</sub> = 30 V	I <sub>CES</sub>	-	-	500	nA
Collector Cutoff Current at V <sub>CB</sub> = 30 V	I <sub>CBO</sub>	-	-	100	nA
Emitter Cutoff Current at V <sub>EB</sub> = 10 V	I <sub>EBO</sub>	-	-	100	nA
Current-Gain-Bandwidth Product at V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA, f = 100 MHz	f <sub>T</sub>	-	200	-	MHz



Dated :15/06/2006